

ML145403 ML145405 ML145404 ML145408 Drivers/Receivers RS 232/EIA-232-E and CCITT V.28

Legacy Device: Motorola MC145403, MC145404, MC145405, MC145408

These devices are silicon gate CMOS ICs that combine both the transmitter and receiver to fulfill the electrical specifications of EIA Standard 232–E and CCITT V.28. The drivers feature true TTL input compatibility, slew rate limiting outputs, 300 Ω power–off source impedance, and output typically switching to within 25% of the supply rails. The receivers can handle up to \pm 25 V while presenting 3 to 7 $k\Omega$ impedance. Hysteresis in the receivers aid in the reception of noisy signals. By combining both drivers and receivers in a single CMOS chip, these devices provide efficient, low–power solutions for both EIA–232–E and V.28 applications.

These devices offer the following performance features:

• Operating Temperature Range $T_A = -40^{\circ}$ to $+85^{\circ}$ C

Drivers

- \pm 5 to \pm 12 V Supply Range
- 300 Ω Power–Off Source Impedance
- Output Current Limiting
- TTL and CMOS Compatible Inputs
- Driver Slew Rate Range Limited to 30 V/µs Maximum

Receivers

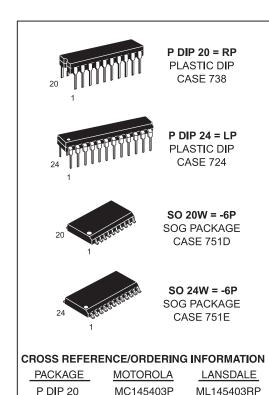
- ± 25 V Input Range
- 3 to 7 k Ω Input Impedance
- 0.8 V of Hysteresis for Enhanced Noise Immunity
- TTL and CMOS Compatible Outputs

Available Driver/Receiver Combinations

Device	Drivers	Receivers	Figure	No. of Pins
ML145403	3	5	1	20
ML145404	4	4	2	20
ML145405	5	3	3	20
ML145408	5	5	4	24

Alternative EIA-232 devices to consider are:

Three Supply
ML145406 (3 x 3)
Single Supply
ML145407 (3 x 3)



Note: Lansdale lead free (**Pb**) product, as it becomes available, will be identified by a part number prefix change from **ML** to **MLE**.

MC145403DW

MC145404P

MC145404DW

MC145405P

MC145405DW

MC145408P

MC145408DW

ML145403-6P

ML145404RP

ML145404-6P

ML145405RP

ML145405-6P

ML145408LP

ML145408-6P

SO 20W

P DIP 20

SO 20W

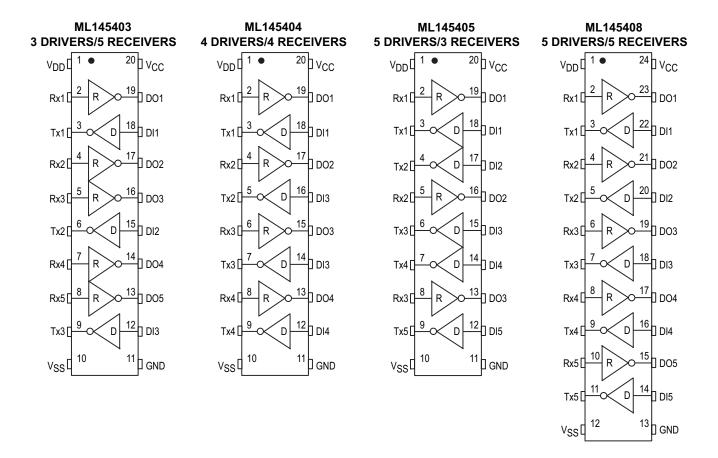
P DIP 20

SO 20W

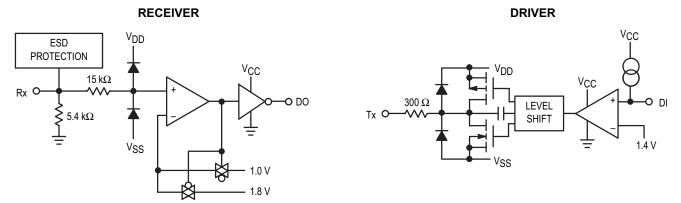
P DIP 24N

SO 24W

PIN ASSIGNMENTS (DIP AND SOG)



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

(Voltages referenced to GND, except where noted)

Rating	Symbol	Value	Unit
DC Supply Voltage (V _{DD} ≥ V _{CC})	V _{DD} V _{SS} V _{CC}	- 0.5 to + 13.5 + 0.5 to - 13.5 - 0.5 to + 6.0	V
Input Voltage Range Rx1 – Rxn DI1 – DIn	VIR	V _{SS} – 15 to V _{DD} + 15 0.5 to V _{CC} + 15	V
DC Current Drain per Pin	I	± 00	mA
Power Dissipation	PD	1	W
Operating Temperature Range	TA	– 40 to + 85	С
Storage Temperature Range	T _{stg}	– 85 to + 150	С

This device contains circuitry to protect the inputs and outputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid applications of any voltage higher than maximum rated voltages to this high impedance circuit.

For proper operation it is recommended that V_{out} and V_{in} be constrained to the ranges described as follows:

Digital I/O: Driver Inputs (DI): $(\mathsf{GND} \leq \mathsf{V}_\mathsf{DI} \leq \mathsf{V}_\mathsf{CC}).$ Receiver Outputs (DO): $(\mathsf{GND} \leq \mathsf{V}_\mathsf{DO} \leq \mathsf{V}_\mathsf{CC}).$ EIA-232 I/O: Driver Outputs (Tx): $(\mathsf{VSS} \leq \mathsf{V}_\mathsf{TX1} - \mathsf{Txn} \leq \mathsf{V}_\mathsf{DD}).$ Receiver Inputs (Rx): $\mathsf{VSS} - 15 \; \mathsf{V} \leq \mathsf{V}_\mathsf{RX1} - \mathsf{Rxn} \leq \mathsf{V}_\mathsf{DD} + 15 \; \mathsf{V}).$ Reliability of operation is enhanced if unual part of the second of the second

Reliability of operation is enhanced if unused outputs are tied off to an appropriate logic voltage level (e.g., either GND or V_{CC} for DI, and GND for Rx).

DC ELECTRICAL CHARACTERISTICS (All polarities referenced to GND = 0 V, T_A = -40 to +85 C)

Parameter		Symbol	Min	Тур	Max	Unit
DC Supply Voltage		V _{DD} V _{SS} V _{CC}	4.5 - 4.5 4.5	5 to 12 - 5 to - 12 5	13.2 - 13.2 5.5	V
Quiescent Supply Current (Outputs Unloaded, Inputs Low)	V _{DD} = + 12 V V _{SS} = - 12 V V _{CC} = + 5 V	I _{DD} Iss Icc		425 - 400 110	635 - 600 200	A

RECEIVER ELECTRICAL SPECIFICATIONS

(Voltage polarities referenced to GND = 0 V, V_{DD} = + 12 V, V_{SS} = - 12 V, T_{A} = - 40 to + 85 C, V_{CC} = + 5 V, ± 10%)

Characteristic		Symbol	Min	Тур	Max	Unit
Input Turn–On Threshold VDO = VOL	Rx1 – Rxn	V _{on}	1.35	1.8	2.35	V
Input Turn–Off Threshold VDO = VOH	Rx1 – Rxn	V _{off}	0.75	1	1.25	V
Input Threshold Hysteresis Δ = V _{on} – V _{off}		V _{hys}	0.6	0.8	_	V
Input Resistance $(V_{SS} - 15 \text{ V}) \le V \text{ Rx1} - \text{Rx} n \le (V_{DD} + 15 \text{ V})$		R _{in}	3	5.4	7	kΩ
High Level Output Voltage V _{Rx} = -3 to -25 V* (DO1 - DO <i>n</i>)	I _{out} = -20 A I _{out} = -1.0 mA	Voн	4.9 3.8	4.9 4.3	_ _	V
Low Level Output Voltage V _{Rx} = + 3 to + 25 V* (DO1 – DO <i>n</i>)	I _{out} = + 2 mA I _{out} = + 4 mA	VOL	_ _	0.02 0.5	0.5 0.7	V

^{*} This is the range of input voltages as specified by EIA-232-E to cause a receiver to be in the high or low.

DRIVER ELECTRICAL SPECIFICATIONS

(Voltage Polarities Referenced to GND = 0 V, V_{DD} = + 12 V, V_{SS} = - 12 V, T_{A} = - 40 to + 85 C, V_{CC} = + 5 V, \pm 10%)

Characteristic	Symbol	Min	Тур	Max	Unit	
Digital Input Voltage Logic 0 Logic 1	DI1 – DI <i>n</i>	V _{IL} VIH	<u> </u>	_ _ _	0.8	V
Input Current VDI = GND VDI = VCC	DI1 – DI <i>n</i>	I _{IL} IIH		7 —	 ± 1.0	A
Output High Voltage $\begin{aligned} &V_{DI} = \text{Logic 0, R}_L = 3 \text{ k}\Omega \\ &V_{DD} = + 5.0 \text{ V, V}_{SS} = -5.0 \text{ V} \\ &V_{DD} = + 6.0 \text{ V, V}_{SS} = -6.0 \text{ V} \\ &V_{DD} = + 12.0 \text{ V, V}_{SS} = -12.0 \text{ V} \end{aligned}$	Tx1 – Tx <i>n</i>	VOH	3.5 4.3 9.2	3.9 4.7 9.5	_ _ _	V
Output Low Voltage* $V_{DI} = \text{Logic 1, R}_{L} = 3 \text{ k}\Omega$ $V_{DD} = +5.0 \text{ V, V}_{SS} = -5.0 \text{ V}$ $V_{DD} = +6.0 \text{ V, V}_{SS} = -6.0 \text{ V}$ $V_{DD} = +12.0 \text{ V, V}_{SS} = -12.0 \text{ V}$	Tx1 – Txn	VoL	- 4 - 4.5 - 10	- 4.3 - 5.2 - 10.3	_ _ _	V
Input Current (Figure 5)	Tx1 – Txn	Z _{off}	300	_	_	Ω
Output Short Circuit Current VDD = + 12 V, VSS = - 12 V Tx Shorted to GND** Tx Shorted to ± 15 V***	Tx1 – Txn	Isc	=	± 22 ± 60	± 60 ± 100	mA

^{*} Voltage specifications are in terms of absolute values.

SWITCHING CHARACTERISTICS (V_{CC} = + 5 V, \pm 10%, V_{DD} = + 12 V, V_{SS} = - 12 V, T_{A} = - 40 to + 85 C; See Figures 2 and 3)

Characteristic	Symbol	Min	Тур	Max	Unit
Drivers					
Propagation Delay Time Tx Low-to-High	^t PLH				ns
$R_L = 3 \text{ k}\Omega$, $C_L = 50 \text{ pF}$		_	500	1000	
High–to–Low R _L = 3 kΩ, C _L = 50 pF	^t PHL	_	700	1000	
Output Slew Rate	SR				V/ s
Minimum Load $R_L = 7 \text{ k}\Omega$, $C_L = 0 \text{ pF}$ (V _{DD} = 6 to 12 V, V _{SS} = -6 to -12 V)		_	± 6	± 30	
Maximum Load $R_L = 3 \text{ k}\Omega$, $C_L = 2500 \text{ pF}$ ($V_{DD} = 12 \text{ V}$, $V_{SS} = -12 \text{ V}$, $V_{CC} = 5 \text{ V}$)		4	_	_	
Receivers (C _L = 50 pF)					
Propagation Delay Time Low–to–High	^t PLH	_	360	610	ns
High-to-Low	t _{PHL}	_	130	610	1
Output Rise Time	t _r	_	250	400	ns
Output Fall Time	t _f	_	40	100	ns

^{**} Specification is for one Tx output pin to be shorted at a time. Should all three driver outputs be shorted simultaneously, device power dissipation limits will be exceeded.

^{***} This condition could exceed package limitations.

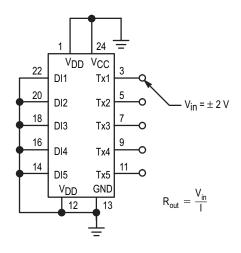
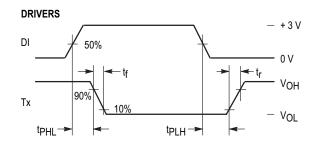


Figure 1. Power–Off Source Resistance Illustrated for ML145408



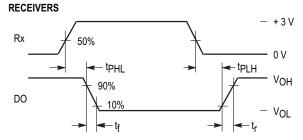


Figure 2. Switching Characteristics

PIN DESCRIPTIONS

VCC Digital Power Supply

The digital supply pin, which is connected to the logic power supply (+ 5.5 V maximum).

GND

Ground

Ground return pin is typically connected to the signal ground pin of the EIA–232–E connector (Pin 7) as well as to the logic power supply ground.

VDD

Most Positive Device Pin

The most positive power supply pin, which is typically + 5 to + 12 V.

DRIVERS

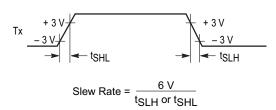


Figure 3. Slew Rate Characteristics

VSS

Most Negative Device Pin

The most negative power supply pin, which is typically -5 to -12 V.

Rx1 - Rxn

Receive Data Input Pins

These are the EIA-232-E receive signal inputs. A voltage between +3 and +25 V is decoded as a space, and causes the corresponding DO pin to swing to ground (0 V). A voltage between -3 and -25 V is decoded as a mark, and causes the corresponding DO pin to swing to V_{CC}.

DO1 – DOn Data Output Pins

These are the receiver digital output pins which swing from V_{CC} to GND. Each output pin is capable of driving one LSTTL input load.

DI1 – DIn Data Input Pins

These are the high impedance digital input pins to the drivers. Input voltage levels on these pins are LSTTL compatible and must be between V_{CC} and GND. A weak pull—up on each input sets all unused DI pins to V_{CC} , causing the corresponding unused driver outputs to be at V_{SS} .

Tx1 – TXn Transmit Data Output Pins

These are the EIA–232–E transmit signal output pins, which swing from V_{DD} to V_{SS} . A logic 1 at the DI input causes the corresponding Tx output to swing to V_{SS} . A logic 0 at the DI input causes the corresponding Tx out to swing to V_{DD} . The actual levels and slew rate achieved will depend on the output loading ($R_L//C_L$).

LEGACY APPLICATION INFORMATION

POWER SUPPLY CONSIDERATIONS

Figure 4 shows a technique to guard against excessive device current.

The diode D1 prevents excessive current from flowing through an internal diode from the V_{CC} pin to the V_{DD} pinwhen V_{DD} < V_{CC} by approximately 0.6 V or greater. This high current condition can exist for a short period of time during power up/down. Additionally, if the + 12 V supply is

switched off while the + 5 V is on and the off supply is a low impedance to ground, the diode D1 will prevent current flow through the internal diode.

The diode D2 is used as a voltage clamp, to prevent VSS from drifting positive to V_{CC} , in the event that power is removed from VSS (Pin 12). If VSS power is removed, and the impedance from the VSS pin to ground is greater than approximately 3 k Ω , this pin will be pulled to V_{CC} by internal circuitry causing excessive current in the V_{CC} pin.

If by design, neither of the above conditions are allowed to exist, then the diodes D1 and D2 are not required.

ESD PROTECTION – CAUTION

ESD protection on IC devices that have their pins accessible to the outside world is essential. High static voltages applied to the pins when someone touches them either directly or in directly can cause damage to gate oxides and transistor junctions by coupling a portion of the energy from the I/O pin to the power supply buses of the IC. This coupling will usually occur through the internal ESD protection diodes. The key to protecting the IC is to shunt as much of the energy to ground as possible before it enters the IC. Figure 4 shows a technique which will clamp the ESD voltage at approximately \pm 15 V using the MMBZ15VDLT1. Any residual voltage which appears on the supply pins is shunted to ground through the capacitors C1 - C3. This scheme has provided protection to the interface part up to \pm 10kV, using the human body model test.

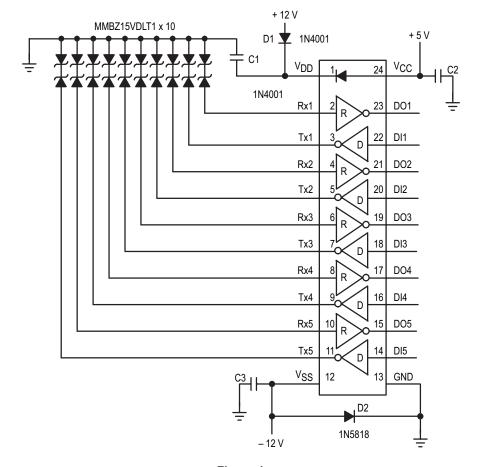
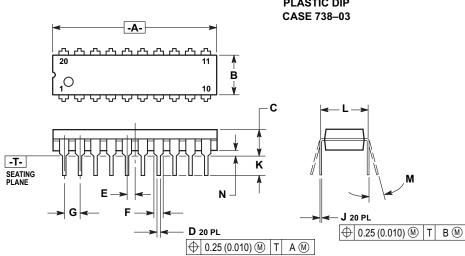


Figure 4.

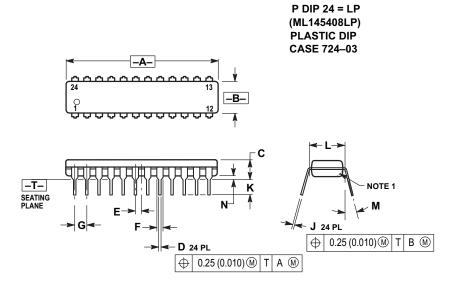
OUTLINE DIMENSIONS

P DIP 20 = RP (ML145403RP, ML145404RP, ML145405RP) **PLASTIC DIP**



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
M	0	15	0	15
N	0.020	0.040	0.51	1.01



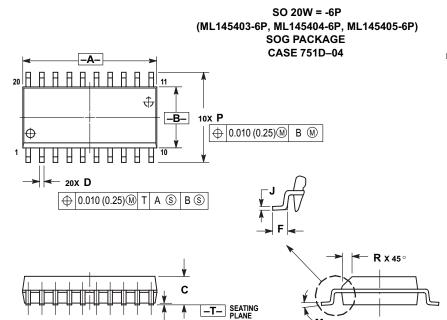
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 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- 3. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 4. CONTROLLING DIMENSION: INCH.

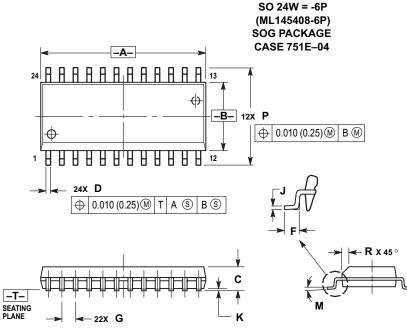
	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.230	1.265	31.25	32.13	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.020	0.38	0.51	
Е	0.050	BSC	1.27	BSC	
F	0.040	0.060	1.02	1.52	
G	0.100	BSC	2.54	BSC	
J	0.007	0.012	0.18	0.30	
K	0.110	0.140	2.80	3.55	
L	0.300	BSC	7.62	BSC	
M	0 °	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

OUTLINE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.150 (0.006) PER SIDE.
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	12.65	12.95	0.499	0.510
В	7.40	7.60	0.292	0.299
С	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27	BSC	0.050	BSC
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0°	7°
Р	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.020



- 10 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	15.25	15.54	0.601	0.612
В	7.40	7.60	0.292	0.299
С	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.41	0.90	0.016	0.035
G	1.27	BSC	0.050	BSC
J	0.23	0.32	0.009	0.013
K	0.13	0.29	0.005	0.011
M	0 °	8°	0 °	8°
Р	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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